

# DSC9A01

## Silicon NPN epitaxial planar type

For low frequency amplification

DSC5A01 in SSMini3 type package

### ■ Features

- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

### ■ Marking Symbol: C8

### ■ Packaging

DSC9A01×0L Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	50	V
Collector-emitter voltage (Base open)	$V_{CEO}$	40	V
Emitter-base voltage (Collector open)	$V_{EBO}$	15	V
Collector current	$I_C$	50	mA
Peak collector current	$I_{CP}$	100	mA
Collector power dissipation	$P_C$	125	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating ambient temperature	$T_{opr}$	-40 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

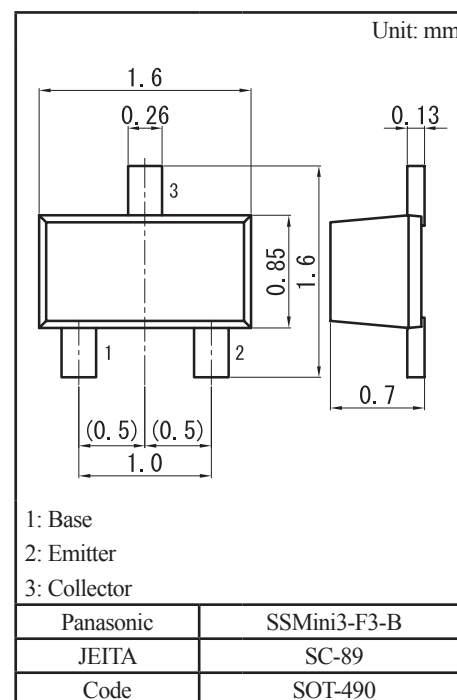
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

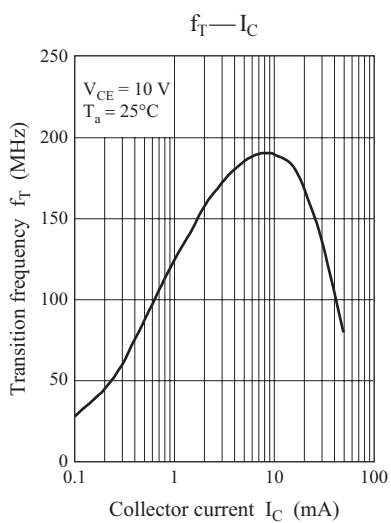
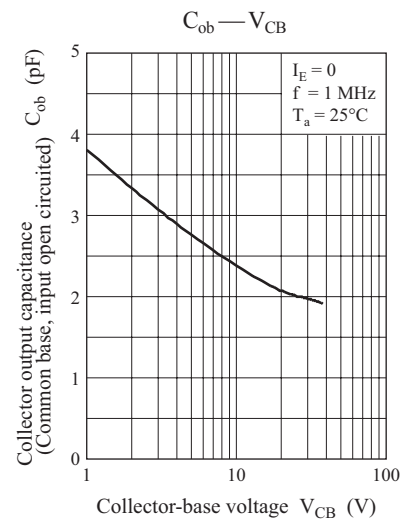
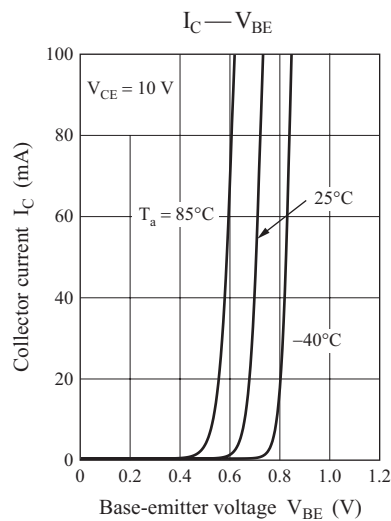
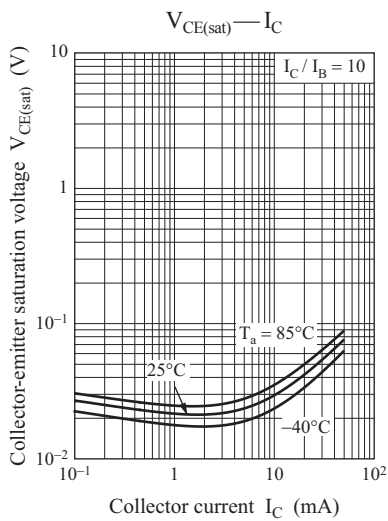
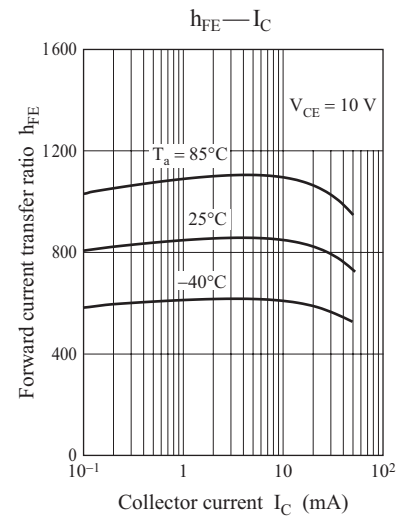
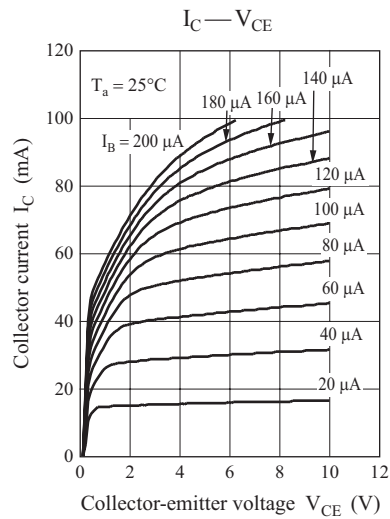
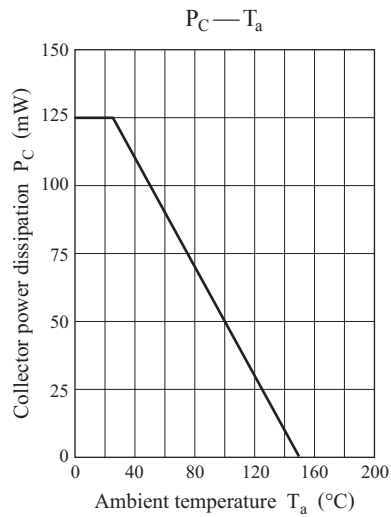
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10\ \mu\text{A}$ , $I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1\ \text{mA}$ , $I_B = 0$	40			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10\ \mu\text{A}$ , $I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20\ \text{V}$ , $I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 20\ \text{V}$ , $I_B = 0$			1	$\mu\text{A}$
Forward current transfer ratio *1	$h_{FE}$	$V_{CE} = 10\ \text{V}$ , $I_C = 2\ \text{mA}$	400		2000	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\ \text{mA}$ , $I_B = 1\ \text{mA}$		0.05	0.20	V
Transition frequency	$f_T$	$V_{CE} = 10\ \text{V}$ , $I_C = 2\ \text{mA}$		150		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Rank classification

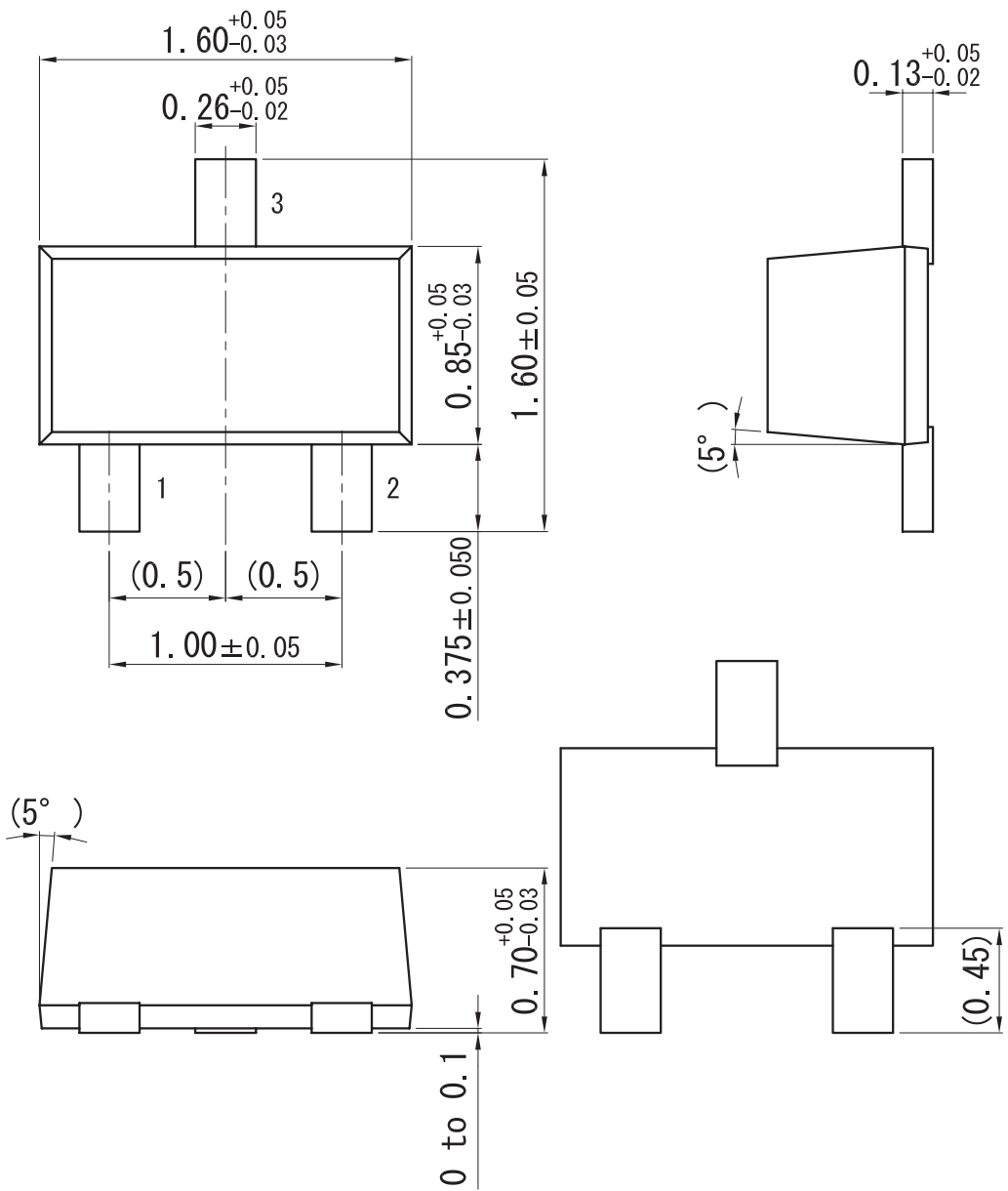
Code	R	S	T
Rank	R	S	T
$h_{FE}$	400 to 800	600 to 1200	1000 to 2000
Marking Symbol	C8R	C8S	C8T



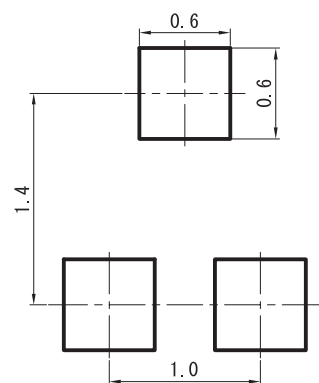


SSMini3-F3-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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